



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. <b>LAM1P152/P0692</b>	Application No.: <b>09/782,446</b>
	Applicant: <b>HO et al.</b>	
	Filing Date <b>February 12, 2001</b>	Group <b>1765</b>

**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
LV	A	5,266,157	11 30 93	Kadomura	156	659.1	10 03 91
LV	B	6,105,588	08 22 00	Li et al.	134	1.1	05 27 98
	C						
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**Foreign Patent or Published Foreign Patent Application**

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
LV	J	01/29879 A2	04/26/01	WIPO	H01L		Yes	
LV	K	JP 09036089	02/07/97	EPO	H01L	21/3065	Yes	
LV	L	0851474 A2	07/01/98	EPO	H01L	21/321	Yes	
	M							
	N							

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
LV	O	James C. Lin et al., "Microwave Imaging of Cerebral Edema", May 1982, Proceedings of the IEEE, Vol. 70, No. 5
LV	P	T. Hasegawa et al., "Copper Dual Damascene Interconnects with Low-k ( $k_{eff} < 3.0$ ) Dielectrics Using FLARE <sup>TM</sup> and an Organo-Silicate Hard Mask", 1999, IEEE
LV	Q	International Search Report, Application No. PCT/US 02/03138, Date of Mailing 12/12/02
Examiner LAN VINH		Date Considered 5/8/2003

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FEB 2 2003

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	Applicant: <b>HO et al.</b>	Group <b>1765</b>
	Filing Date <b>February 12, 2001</b>	FEB 2 6 2003 <b>PG 1700</b>

**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
LV	A	5,970,376	10/19/99	Chen	438	637	12/29/97
LV	B	6,040,248	03/21/00	Chen et al.	438	725	06/24/98
	C						
	D						
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	I						

**Foreign Patent or Published Foreign Patent Application**

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
LV	J	09036089	02/07/97	Japan	H01L	21/3065	X	
	K							
	L							
	M							
	N							

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
LV	O	Eto et al., "High Selectivity Photoresist Ashing by the Addition of NH <sub>3</sub> to CF <sub>4</sub> /O <sub>2</sub> or CHF <sub>3</sub> /O <sub>2</sub> ". SID 99 Digest, pages 844-847
LV	P	Delsol et al., "Transformer Coupled Plasma Dielectric Etch for 0.25 $\mu$ m Technologies", Elsevier, Microelectronic Engineering 50 (2000), pages 75-80
LV	Q	International Search Report, 11/20/02
Examiner LAN VINH		Date Considered 5/8/2003

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